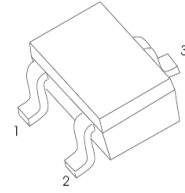


## PNP Plastic-Encapsulate Transistors

### FEATURES

- Epitaxial Planar Die Construction
- Complementary NPN Type Available
- Also Available in Lead Free Version

### MARKING:2A



**SOT-523**

1. BASE 2. EMITTER 3. COLLECTOR

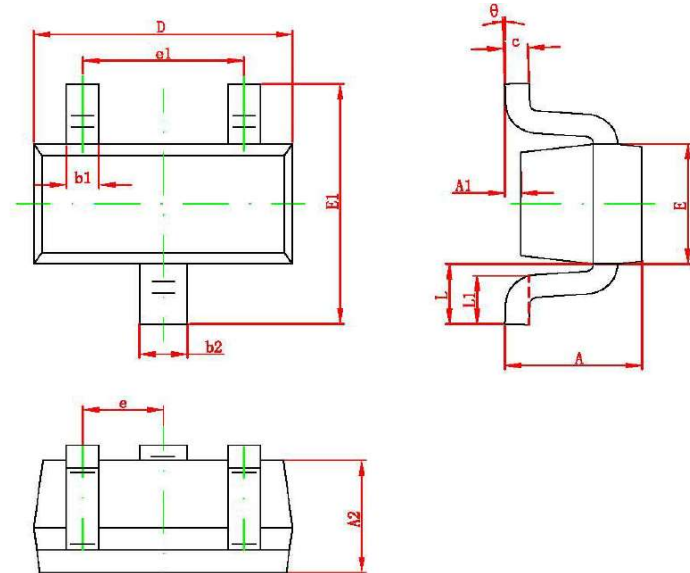
### MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CB0}$	Collector-Base Voltage	-40	V
$V_{CEO}$	Collector-Emitter Voltage	-40	V
$V_{EBO}$	Emitter-Base Voltage	-5.0	V
$I_C$	Collector Current -Continuous	-200	mA
$P_C$	Collector Power Dissipation	150	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	833	$^\circ\text{C}/\text{W}$
$T_J$	Operating Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-30\text{V}, I_E=0$			-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-5\text{V}, I_C=0$			-0.1	$\mu\text{A}$
Collector cut-off current	$I_{CEX}$	$V_{CB}=-30\text{V}, V_{BE(off)}=-3\text{V}$			-0.05	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE}=-1\text{V}, I_C=-0.1\text{mA}$	60			
	$h_{FE(2)}$	$V_{CE}=-1\text{V}, I_C=-1\text{mA}$	80			
	$h_{FE(3)}$	$V_{CE}=-1\text{V}, I_C=-10\text{mA}$	100		300	
	$h_{FE(4)}$	$V_{CE}=-1\text{V}, I_C=-50\text{mA}$	60			
	$h_{FE(5)}$	$V_{CE}=-1\text{V}, I_C=-100\text{mA}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C=-10\text{mA}, I_B=-1\text{mA}$			-0.25	V
	$V_{CE(sat)2}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$			-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	$I_C=-10\text{mA}, I_B=-1\text{mA}$	-0.65		-0.85	V
	$V_{BE(sat)2}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$			-0.95	V
Transition frequency	$f_T$	$V_{CE}=-20\text{V}, I_C=-10\text{mA}, f=100\text{MHz}$	250			MHz
Collector output capacitance	$C_{obo}$	$V_{CB}=-5\text{V}, I_E=0, f=1\text{MHz}$			4.5	pF
Input capacitance	$C_{iob}$	$V_{EB}=-0.5\text{V}, I_E=0, f=1\text{MHz}$			10	pF
Noise figure	NF	$V_{CE}=-5\text{V}, I_C=0.1\text{mA}$ ,			4	dB
Delay time	$t_d$	$f$ $V_{CC}=-3\text{V}, V_{BE(OFF)}=-0.5\text{V}$			35	ns
Rise time	$t_r$	$I_C=-10\text{mA}, I_{B1}=-1\text{mA}$			35	ns
Storage time	$t_s$	$V_{CC}=-3\text{V}, I_C=-10\text{mA}$			225	ns
Fall time	$t_f$	$I_{B1}=I_{B2}=-1\text{mA}$			75	ns

## SOT-523 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°		8°	